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Summary

The Xilinx® Kintex® UltraScale+™ FPGAs are available in -3, -2, -1 speed grades, with -3E devices having the highest performance. The -2LE and -1LI devices can operate at a V_{CCINT} voltage at 0.85V or 0.72V and provide lower maximum static power. When operated at V_{CCINT} = 0.85V, using -2LE and -1LI devices, the speed specification for the L devices is the same as the -2I or -1I speed grades. When operated at V_{CCINT} = 0.72V, the -2LE and -1LI performance and static and dynamic power is reduced.

DC and AC characteristics are specified in extended (E) and industrial (I) temperature ranges. Except the operating temperature range or unless otherwise noted, all the DC and AC electrical parameters are the same for a particular speed grade (that is, the timing characteristics of a -1 speed grade extended device are the same as for a -1 speed grade industrial device). However, only selected speed grades and/or devices are available in each temperature range.

All supply voltage and junction temperature specifications are representative of worst-case conditions. The parameters included are common to popular designs and typical applications.

This data sheet, part of an overall set of documentation on the Kintex UltraScale+ FPGAs, is available on the Xilinx website at www.xilinx.com/documentation.

DC Characteristics

Absolute Maximum Ratings

Table 1: **Absolute Maximum Ratings**[1]

Symbol	Description	Min	Max	Units
FPGA Logic				
V_{CCINT}	Internal supply voltage.	−0.500	1.000	V
V_{CCINT_IO}[2]	Internal supply voltage for the I/O banks.	−0.500	1.000	V
V_{CCAUX}	Auxiliary supply voltage.	−0.500	2.000	V
V_{CCBRAM}	Supply voltage for the block RAM memories.	−0.500	1.000	V
V_{CCO}	Output drivers supply voltage for HD I/O banks.	−0.500	3.400	V
	Output drivers supply voltage for HP I/O banks.	−0.500	2.000	V
V_{CCAUX_IO}[3]	Auxiliary supply voltage for the I/O banks.	−0.500	2.000	V
V_{REF}	Input reference voltage.	−0.500	2.000	V
V_{IN}[4][6][7]	I/O input voltage for HD I/O banks.[5]	−0.550	V_{CCO} + 0.550	V
	I/O input voltage for HP I/O banks.	−0.550	V_{CCO} + 0.550	V

Table 1: **Absolute Maximum Ratings**[1] *(Cont'd)*

Symbol	Description	Min	Max	Units
V_{BATT}	Key memory battery backup supply.	−0.500	2.000	V
I_{DC}	Available output current at the pad.	−20	20	mA
I_{RMS}	Available RMS output current at the pad.	−20	20	mA
GTH or GTY Transceiver				
$V_{MGTAVCC}$	Analog supply voltage for transceiver circuits.	−0.500	1.000	V
$V_{MGTAVTT}$	Analog supply voltage for transceiver termination circuits.	−0.500	1.300	V
$V_{MGTVCCAUX}$	Auxiliary analog Quad PLL (QPLL) voltage supply for transceivers.	−0.500	1.900	V
$V_{MGTREFCLK}$	Transceiver reference clock absolute input voltage.	−0.500	1.300	V
$V_{MGTAVTTRCAL}$	Analog supply voltage for the resistor calibration circuit of the transceiver column.	−0.500	1.300	V
V_{IN}	Receiver (RXP/RXN) and transmitter (TXP/TXN) absolute input voltage.	−0.500	1.200	V
$I_{DCIN-FLOAT}$	DC input current for receiver input pins DC coupled RX termination = floating.[8]	–	10	mA
$I_{DCIN-MGTAVTT}$	DC input current for receiver input pins DC coupled RX termination = $V_{MGTAVTT}$.	–	10	mA
$I_{DCIN-GND}$	DC input current for receiver input pins DC coupled RX termination = GND.[9]	–	0	mA
$I_{DCIN-PROG}$	DC input current for receiver input pins DC coupled RX termination = programmable.[10]	–	0	mA
$I_{DCOUT-FLOAT}$	DC output current for transmitter pins DC coupled RX termination = floating.	–	6	mA
$I_{DCOUT-MGTAVTT}$	DC output current for transmitter pins DC coupled RX termination = $V_{MGTAVTT}$.	–	6	mA
System Monitor				
V_{CCADC}	System Monitor supply relative to GNDADC.	0.500	2.000	V
V_{REFP}	System Monitor reference input relative to GNDADC.	0.500	2.000	V

Table 1: **Absolute Maximum Ratings**[1] *(Cont'd)*

Symbol	Description	Min	Max	Units
Temperature				
T_{STG}	Storage temperature (ambient).	−65	150	°C
T_{SOL}	Maximum soldering temperature.[12]	–	260	°C
T_j	Maximum junction temperature.[12]	–	125	°C

Notes:
1. Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.
2. V_{CCINT_IO} must be connected to V_{CCBRAM}.
3. V_{CCAUX_IO} must be connected to V_{CCAUX}.
4. The lower absolute voltage specification always applies.
5. If V_{CCO} is 3.3V, the maximum voltage is 3.4V.
6. For I/O operation, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).
7. When operating outside of the recommended operating conditions, refer to Table 4 and Table 5 for maximum overshoot and undershoot specifications.
8. AC coupled operation is not supported for RX termination = floating.
9. For GTY transceivers, DC coupled operation is not supported for RX termination = GND.
10. DC coupled operation is not supported for RX termination = programmable.
11. For more information on supported GTH or GTY transceiver terminations see the *UltraScale Architecture GTH Transceiver User Guide* (UG576) or *UltraScale Architecture GTY Transceiver User Guide* (UG578).
12. For soldering guidelines and thermal considerations, see the *UltraScale and UltraScale+ FPGAs Packaging and Pinout Specifications* (UG575).

Recommended Operating Conditions

Table 2: **Recommended Operating Conditions**[1][2]

Symbol	Description	Min	Typ	Max	Units
FPGA Logic					
V_{CCINT}	Internal supply voltage.	0.825	0.850	0.876	V
	For -1LI and -2LE devices (V_{CCINT} = 0.72V): internal supply voltage.	0.698	0.720	0.742	V
	For -3E devices: internal supply voltage.	0.873	0.900	0.927	V
V_{CCINT_IO}[3]	Internal supply voltage for the I/O banks.	0.825	0.850	0.876	V
	For -1LI and -2LE devices (V_{CCINT} = 0.72V): internal supply voltage for the I/O banks.	0.825	0.850	0.876	V
	For -3E devices: internal supply voltage for the I/O banks.	0.873	0.900	0.927	V
V_{CCBRAM}	Block RAM supply voltage.	0.825	0.850	0.876	V
	For -3E devices: block RAM supply voltage.	0.873	0.900	0.927	V
V_{CCAUX}	Auxiliary supply voltage.	1.746	1.800	1.854	V
V_{CCO}[4][5]	Supply voltage for HD I/O banks.	1.140	–	3.400	V
	Supply voltage for HP I/O banks.	0.950	–	1.900	V
V_{CCAUX_IO}[6]	Auxiliary I/O supply voltage.	1.746	1.800	1.854	V
V_{IN}[7]	I/O input voltage.	−0.200	–	V_{CCO} + 0.200	V
I_{IN}[8]	Maximum current through any pin in a powered or unpowered bank when forward biasing the clamp diode.	–	–	10	mA
V_{BATT}[9]	Battery voltage	1.000	–	1.890	V

Table 2: **Recommended Operating Conditions**[1][2] *(Cont'd)*

Symbol	Description	Min	Typ	Max	Units
GTH or GTY Transceiver					
$V_{MGTAVCC}$[10]	Analog supply voltage for the GTH or GTY transceiver.	0.873	0.900	0.927	V
$V_{MGTAVTT}$[10]	Analog supply voltage for the GTH or GTY transmitter and receiver termination circuits.	1.164	1.200	1.236	V
$V_{MGTVCCAUX}$[10]	Auxiliary analog QPLL voltage supply for the transceivers.	1.746	1.800	1.854	V
$V_{MGTAVTTRCAL}$[10]	Analog supply voltage for the resistor calibration circuit of the GTH or GTY transceiver column.	1.164	1.200	1.236	V
SYSMON					
V_{CCADC}	SYSMON supply relative to GNDADC.	1.746	1.800	1.854	V
V_{REFP}	SYSMON externally supplied reference voltage relative to GNDADC.	1.200	1.250	1.300	V
Temperature					
T_j[12]	Junction temperature operating range for extended (E) temperature devices.[11]	0	–	100	°C
	Junction temperature operating range for industrial (I) temperature devices.	–40	–	100	°C
	Junction temperature operating range for eFUSE programming.[13]	–40	–	125	°C

Notes:
1. All voltages are relative to GND.
2. For the design of the power distribution system consult *UltraScale Architecture PCB Design Guide* (UG583).
3. V_{CCINT_IO} must be connected to V_{CCBRAM}.
4. For V_{CCO_0}, the minimum recommended operating voltage for power on and during configuration is 1.425V. After configuration, data is retained even if V_{CCO} drops to 0V.
5. Includes V_{CCO} of 1.0V (HP I/O only), 1.2V, 1.35V, 1.5V, 1.8V, 2.5V (HD I/O only) at ±5%, and 3.3V (HD I/O only) at +3/−5%.
6. V_{CCAUX_IO} must be connected to V_{CCAUX}.
7. The lower absolute voltage specification always applies.
8. A total of 200 mA per bank should not be exceeded.
9. If battery is not used, connect V_{BATT} to either GND or V_{CCAUX}.
10. Each voltage listed requires filtering as described in *UltraScale Architecture GTH Transceiver User Guide* (UG576) or *UltraScale Architecture GTY Transceiver User Guide* (UG578).
11. Devices labeled with the speed/temperature grade of -2LE normally operate under Extended (E) temperature grade specifications with a maximum junction temperature of 100°C. However, E temperature grade devices can operate for a for a limited time at a junction temperature of 110°C. Timing parameters adhere to the same speed file at 110°C as they do at 100°C, regardless of operating voltage (nominal voltage of 0.85V or a low-voltage of 0.72V). Operation at Tj = 110°C is limited to 1% of the device lifetime and can occur sequentially or at regular intervals as long as the total time does not exceed 1% of the device lifetime.
12. Xilinx recommends measuring the Tj of a device using the system monitor as described in the *UltraScale Architecture System Monitor User Guide* (UG580). The SYSMON temperature measurement errors (that are described in Table 76) must be accounted for in your design. For example, by using an external reference of 1.25V, when SYSMON reports 97°C, there is a measurement error ±3°C. A reading of 97°C is considered the maximum adjusted Tj (100°C − 3°C = 97°C).
13. Do not program eFUSE during device configuration (e.g., during configuration, during configuration readback, or when readback CRC is active).

DC Characteristics Over Recommended Operating Conditions

Table 3: **DC Characteristics Over Recommended Operating Conditions**

Symbol	Description	Min	Typ[1]	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost).	0.68	–	–	V
V_{DRAUX}	Data retention V_{CCAUX} voltage (below which configuration data might be lost).	1.5	–	–	V
I_{REF}	V_{REF} leakage current per pin.	–	–	15	µA
I_L	Input or output leakage current per pin (sample-tested).[2]	–	–	15	µA
C_{IN}[3]	Die input capacitance at the pad (HP I/O).	–	–	3.1	pF
	Die input capacitance at the pad (HD I/O).	–	–	4.75	pF
I_{RPU}	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 3.3V.	75	–	190	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 2.5V.	50	–	169	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.8V.	60	–	120	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.5V.	30	–	120	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.2V.	10	–	100	µA
I_{RPD}	Pad pull-down (when selected) at V_{IN} = 3.3V.	60	–	200	µA
	Pad pull-down (when selected) at V_{IN} = 1.8V.	29	–	120	µA
$I_{CCADCON}$	Analog supply current for the SYSMON circuits in the power-up state.	–	–	8	mA
$I_{CCADCOFF}$	Analog supply current for the SYSMON circuits in the power-down state.	–	–	1.5	mA
I_{BATT}[4][5]	Battery supply current at V_{BATT} = 1.89V.	–	–	650	nA
	Battery supply current at V_{BATT} = 1.20V.	–	–	150	nA
I_{PFS}[6]	V_{CCAUX} additional supply current during eFUSE programming.	–	–	115	mA
Calibrated programmable on-die termination (DCI) in HP I/O banks[7] *(measured per JEDEC specification).*					
R[9]	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_40.	–10%[8]	40	+10%[8]	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_48.	–10%[8]	48	+10%[8]	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_60.	–10%[8]	60	+10%[8]	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_40.	–10%[8]	40	+10%[8]	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_48.	–10%[8]	48	+10%[8]	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_60.	–10%[8]	60	+10%[8]	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_120.	–10%[8]	120	+10%[8]	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_240.	–10%[8]	240	+10%[8]	Ω

Table 3: **DC Characteristics Over Recommended Operating Conditions** *(Cont'd)*

Symbol	Description	Min	Typ[1]	Max	Units
— *Uncalibrated programmable on-die termination in HP I/O banks (measured per JEDEC specification).*					
R[9]	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_40.	−50%	40	+50%	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_48.	−50%	48	+50%	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_60.	−50%	60	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_40.	−50%	40	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_48.	−50%	48	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_60.	−50%	60	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_120.	−50%	120	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_240.	−50%	240	+50%	Ω
— *Uncalibrated programmable on-die termination in HD I/O banks (measured per JEDEC specification).*					
R[9]	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_48.	−50%	48	+50%	Ω
Internal V_{REF}	50% V_{CCO}	V_{CCO} x 0.49	V_{CCO} x 0.50	V_{CCO} x 0.51	V
	70% V_{CCO}	V_{CCO} x 0.69	V_{CCO} x 0.70	V_{CCO} x 0.71	V
Differential termination	Programmable differential termination (TERM_100) for HP I/O banks.	−35%	100	+35%	Ω
n	Temperature diode ideality factor.	–	1.026	–	–
r	Temperature diode series resistance.	–	2	–	Ω

Notes:
1. Typical values are specified at nominal voltage, 25°C.
2. For HP I/O banks with a V_{CCO} of 1.8V and separated V_{CCO} and V_{CCAUX_IO} power supplies, the I_L maximum current is 70 µA.
3. This measurement represents the die capacitance at the pad, not including the package.
4. Maximum value specified for worst case process at 25°C.
5. I_{BATT} is measured when the battery-backed RAM (BBRAM) is enabled.
6. Do not program eFUSE during device configuration (e.g., during configuration, during configuration readback, or when readback CRC is active).
7. If VRP resides at a different bank (DCI cascade), the range increases to ±15%.
8. VRP resistor tolerance is (240Ω ±1%)
9. On-die input termination resistance, for more information see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).

V_{IN} Maximum Allowed AC Voltage Overshoot and Undershoot

Table 4: **V_{IN} Maximum Allowed AC Voltage Overshoot and Undershoot for HD I/O Banks**[1]

AC Voltage Overshoot	% of UI at −40°C to 100°C	AC Voltage Undershoot	% of UI at −40°C to 100°C
V_{CCO} + 0.30	100%	−0.30	100%
V_{CCO} + 0.35	100%	−0.35	90%
V_{CCO} + 0.40	100%	−0.40	78%
V_{CCO} + 0.45	100%	−0.45	40%
V_{CCO} + 0.50	100%	−0.50	24%
V_{CCO} + 0.55	100%	−0.55	18.0%
V_{CCO} + 0.60	100%	−0.60	13.0%
V_{CCO} + 0.65	100%	−0.65	10.8%
V_{CCO} + 0.70	92%	−0.70	9.0%
V_{CCO} + 0.75	92%	−0.75	7.0%
V_{CCO} + 0.80	92%	−0.80	6.0%
V_{CCO} + 0.85	92%	−0.85	5.0%
V_{CCO} + 0.90	92%	−0.90	4.0%
V_{CCO} + 0.95	92%	−0.95	2.5%

Notes:
1. A total of 200 mA per bank should not be exceeded.

Table 5: **V_{IN} Maximum Allowed AC Voltage Overshoot and Undershoot for HP I/O Banks**[1][2]

AC Voltage Overshoot	% of UI at −40°C to 100°C	AC Voltage Undershoot	% of UI at −40°C to 100°C
V_{CCO} + 0.30	100%	−0.30	100%
V_{CCO} + 0.35	100%	−0.35	90%
V_{CCO} + 0.40	92%	−0.40	92%
V_{CCO} + 0.45	50%	−0.45	50%
V_{CCO} + 0.50	20%	−0.50	20%
V_{CCO} + 0.55	10%	−0.55	10%
V_{CCO} + 0.60	6%	−0.60	6%
V_{CCO} + 0.65	2%	−0.65	2%
V_{CCO} + 0.70	2%	−0.70	2%

Notes:
1. A total of 200 mA per bank should not be exceeded.
2. For UI smaller than 20 μs.

Quiescent Supply Current

Table 6: **Typical Quiescent Supply Current**[1][2][3]

Symbol	Description	Device	Speed Grade and V_{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
I_{CCINTQ}	Quiescent V_{CCINT} supply current.	XCKU3P	1242	1181	1181	1037	1037	mA
		XCKU5P	1242	1181	1181	1037	1037	mA
		XCKU9P	1592	1523	1523	1356	1356	mA
		XCKU11P	1780	1693	1693	1486	1486	mA
		XCKU13P	1950	1864	1864	1658	1658	mA
		XCKU15P	2677	2559	2559	2275	2275	mA
I_{CCINT_IOQ}	Quiescent V_{CCINT_IO} supply current.	XCKU3P	61	59	59	59	59	mA
		XCKU5P	61	59	59	59	59	mA
		XCKU9P	61	59	59	59	59	mA
		XCKU11P	120	115	115	115	115	mA
		XCKU13P	61	59	59	59	59	mA
		XCKU15P	164	158	158	158	158	mA
I_{CCOQ}	Quiescent V_{CCO} supply current.	All devices	1	1	1	1	1	mA
I_{CCAUXQ}	Quiescent V_{CCAUX} supply current.	XCKU3P	153	153	153	153	153	mA
		XCKU5P	153	153	153	153	153	mA
		XCKU9P	227	227	227	227	227	mA
		XCKU11P	255	255	255	255	255	mA
		XCKU13P	266	266	266	266	266	mA
		XCKU15P	396	396	396	396	396	mA
I_{CCAUX_IOQ}	Quiescent V_{CCAUX_IO} supply current.	XCKU3P	32	32	32	32	32	mA
		XCKU5P	32	32	32	32	32	mA
		XCKU9P	33	33	33	33	33	mA
		XCKU11P	56	56	56	56	56	mA
		XCKU13P	33	33	33	33	33	mA
		XCKU15P	74	74	74	74	74	mA
$I_{CCBRAMQ}$	Quiescent V_{CCBRAM} supply current.	XCKU3P	18	17	17	17	17	mA
		XCKU5P	18	17	17	17	17	mA
		XCKU9P	25	24	24	24	24	mA
		XCKU11P	23	22	22	22	22	mA
		XCKU13P	29	28	28	28	28	mA
		XCKU15P	37	35	35	35	35	mA

Notes:

1. Typical values are specified at nominal voltage, 85°C junction temperatures (T_j) with single-ended SelectIO™ resources.
2. Typical values are for blank configured devices with no output current loads, no active input pull-up resistors, all I/O pins are 3-state and floating.
3. Use the Xilinx Power Estimator (XPE) spreadsheet tool (download at www.xilinx.com/power) to estimate static power consumption for conditions other than those specified.

Power-On/Off Power Supply Sequencing

The recommended power-on sequence is V_{CCINT}, V_{CCINT_IO}/V_{CCBRAM}, V_{CCAUX}/V_{CCAUX_IO}, and V_{CCO} to achieve minimum current draw and ensure that the I/Os are 3-stated at power-on. The recommended power-off sequence is the reverse of the power-on sequence. If V_{CCINT} and V_{CCINT_IO}/V_{CCBRAM} have the same recommended voltage levels, they can be powered by the same supply and ramped simultaneously. V_{CCINT_IO} must be connected to V_{CCBRAM}. If V_{CCAUX}/V_{CCAUX_IO} and V_{CCO} have the same recommended voltage levels, they can be powered by the same supply and ramped simultaneously. V_{CCAUX} and V_{CCAUX_IO} must be connected together. V_{CCADC} and V_{REF} can be powered at any time and have no power-up sequencing requirements.

The recommended power-on sequence to achieve minimum current draw for the GTH or GTY transceivers is V_{CCINT}, $V_{MGTAVCC}$, $V_{MGTAVTT}$ OR $V_{MGTAVCC}$, V_{CCINT}, $V_{MGTAVTT}$. There is no recommended sequencing for $V_{MGTVCCAUX}$. Both $V_{MGTAVCC}$ and V_{CCINT} can be ramped simultaneously. The recommended power-off sequence is the reverse of the power-on sequence to achieve minimum current draw.

If these recommended sequences are not met, current drawn from $V_{MGTAVTT}$ can be higher than specifications during power-up and power-down.

Power Supply Requirements

Table 7 shows the minimum current, in addition to I_{CCQ} maximum, required by each Kintex UltraScale+ FPGA for proper power-on and configuration. If the current minimums shown in Table 7 are met, the device powers on after all supplies have passed through their power-on reset threshold voltages. The device must not be configured until after V_{CCINT} is applied. Once initialized and configured, use the Xilinx Power Estimator (XPE) tools to estimate current drain on these supplies.

Table 7: **Power-on Current by Device[1]**

Device	$I_{CCINTMIN}$	$I_{CCINT\_IOMIN} + I_{CCBRAMMIN}$	I_{CCOMIN}	$I_{CCAUXMIN} + I_{CCAUX\_IOMIN}$	Units
XCKU3P	$I_{CCINTQ} + 770$	$I_{CCBRAMQ} + I_{CCINT\_IOQ} + 229$	$I_{CCOQ} + 50$	$I_{CCAUXQ} + I_{CCAUX\_IOQ} + 386$	mA
XCKU5P	$I_{CCINTQ} + 770$	$I_{CCBRAMQ} + I_{CCINT\_IOQ} + 305$	$I_{CCOQ} + 50$	$I_{CCAUXQ} + I_{CCAUX\_IOQ} + 515$	mA
XCKU9P	$I_{CCINTQ} + 1800$	$I_{CCBRAMQ} + I_{CCINT\_IOQ} + 600$	$I_{CCOQ} + 50$	$I_{CCAUXQ} + I_{CCAUX\_IOQ} + 650$	mA
XCKU11P	$I_{CCINTQ} + 1961$	$I_{CCBRAMQ} + I_{CCINT\_IOQ} + 654$	$I_{CCOQ} + 55$	$I_{CCAUXQ} + I_{CCAUX\_IOQ} + 709$	mA
XCKU13P	$I_{CCINTQ} + 2242$	$I_{CCBRAMQ} + I_{CCINT\_IOQ} + 748$	$I_{CCOQ} + 63$	$I_{CCAUXQ} + I_{CCAUX\_IOQ} + 810$	mA
XCKU15P	$I_{CCINTQ} + 3433$	$I_{CCBRAMQ} + I_{CCINT\_IOQ} + 1145$	$I_{CCOQ} + 96$	$I_{CCAUXQ} + I_{CCAUX\_IOQ} + 1240$	mA

Notes:
1. Use the Xilinx Power Estimator (XPE) spreadsheet tool (download at www.xilinx.com/power) to estimate power-on current for all supplies.

Table 8 shows the power supply ramp time.

Table 8: **Power Supply Ramp Time**

Symbol	Description	Min	Max	Units
T_{VCCINT}	Ramp time from GND to 95% of V_{CCINT}.	0.2	40	ms
T_{VCCINT_IO}	Ramp time from GND to 95% of V_{CCINT_IO}.	0.2	40	ms
T_{VCCO}	Ramp time from GND to 95% of V_{CCO}.	0.2	40	ms
T_{VCCAUX}	Ramp time from GND to 95% of V_{CCAUX}.	0.2	40	ms
$T_{VCCBRAM}$	Ramp time from GND to 95% of V_{CCBRAM}.	0.2	40	ms
$T_{MGTAVCC}$	Ramp time from GND to 95% of $V_{MGTAVCC}$.	0.2	40	ms
$T_{MGTAVTT}$	Ramp time from GND to 95% of $V_{MGTAVTT}$.	0.2	40	ms
$T_{MGTVCCAUX}$	Ramp time from GND to 95% of $V_{MGTVCCAUX}$.	0.2	40	ms

DC Input and Output Levels

Values for V_{IL} and V_{IH} are recommended input voltages. Values for I_{OL} and I_{OH} are guaranteed over the recommended operating conditions at the V_{OL} and V_{OH} test points. Only selected standards are tested. These are chosen to ensure that all standards meet their specifications. The selected standards are tested at a minimum V_{CCO} with the respective V_{OL} and V_{OH} voltage levels shown. Other standards are sample tested.

Table 9: **SelectIO DC Input and Output Levels For HD I/O Banks**[1][2][3]

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
HSTL_I	−0.300	V_{REF} − 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} − 0.400	8.0	−8.0
HSTL_I_18	−0.300	V_{REF} − 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} − 0.400	8.0	−8.0
HSUL_12	−0.300	V_{REF} − 0.130	V_{REF} + 0.130	V_{CCO} + 0.300	20% V_{CCO}	80% V_{CCO}	0.1	−0.1
LVCMOS12	−0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.400	V_{CCO} − 0.400	Note 4	Note 4
LVCMOS15	−0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} − 0.450	Note 5	Note 5
LVCMOS18	−0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} − 0.450	Note 5	Note 5
LVCMOS25	−0.300	0.700	1.700	V_{CCO} + 0.300	0.400	V_{CCO} − 0.400	Note 5	Note 5
LVCMOS33	−0.300	0.800	2.000	3.400	0.400	V_{CCO} − 0.400	Note 5	Note 5
LVTTL	−0.300	0.800	2.000	3.400	0.400	2.400	Note 5	Note 5
SSTL12	−0.300	V_{REF} − 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	$V_{CCO}/2$ − 0.150	$V_{CCO}/2$ + 0.150	14.25	−14.25
SSTL135	−0.300	V_{REF} − 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	$V_{CCO}/2$ − 0.150	$V_{CCO}/2$ + 0.150	8.9	−8.9
SSTL135_II	−0.300	V_{REF} − 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	$V_{CCO}/2$ − 0.150	$V_{CCO}/2$ + 0.150	13.0	−13.0
SSTL15	−0.300	V_{REF} − 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	$V_{CCO}/2$ − 0.175	$V_{CCO}/2$ + 0.175	8.9	−8.9
SSTL15_II	−0.300	V_{REF} − 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	$V_{CCO}/2$ − 0.175	$V_{CCO}/2$ + 0.175	13.0	−13.0
SSTL18_I	−0.300	V_{REF} − 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	$V_{CCO}/2$ − 0.470	$V_{CCO}/2$ + 0.470	8.0	−8.0
SSTL18_II	−0.300	V_{REF} − 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	$V_{CCO}/2$ − 0.600	$V_{CCO}/2$ + 0.600	13.4	−13.4
MIPI_DPHY_DCI_LP[6]	−0.300	0.550	0.880	V_{CCO} + 0.300	0.050	1.100	0.01	−0.01

Notes:
1. Tested according to relevant specifications.
2. Standards specified using the default I/O standard configuration. For details, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).
3. POD10 and POD12 DC input and output levels are shown in Table 11, Table 15, Table 16, and Table 17.
4. Supported drive strengths of 4, 8, or 12 mA in HD I/O banks.
5. Supported drive strengths of 4, 8, 12, or 16 mA in HD I/O banks.
6. Low-power option for MIPI_DPHY_DCI.

Table 10: **SelectIO DC Input and Output Levels for HP I/O Banks**[1][2][3]

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
HSTL_I	−0.300	V_{REF} − 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} − 0.400	5.8	−5.8
HSTL_I_12	−0.300	V_{REF} − 0.080	V_{REF} + 0.080	V_{CCO} + 0.300	25% V_{CCO}	75% V_{CCO}	4.1	−4.1
HSTL_I_18	−0.300	V_{REF} − 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} − 0.400	6.2	−6.2
HSUL_12	−0.300	V_{REF} − 0.130	V_{REF} + 0.130	V_{CCO} + 0.300	20% V_{CCO}	80% V_{CCO}	0.1	−0.1
LVCMOS12	−0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.400	V_{CCO} − 0.400	Note 4	Note 4
LVCMOS15	−0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} − 0.450	Note 5	Note 5
LVCMOS18	−0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} − 0.450	Note 5	Note 5
LVDCI_15	−0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} − 0.450	7.0	−7.0
LVDCI_18	−0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} − 0.450	7.0	−7.0
SSTL12	−0.300	V_{REF} − 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 − 0.150	V_{CCO}/2 + 0.150	8.0	−8.0
SSTL135	−0.300	V_{REF} − 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	V_{CCO}/2 − 0.150	V_{CCO}/2 + 0.150	9.0	−9.0
SSTL15	−0.300	V_{REF} − 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 − 0.175	V_{CCO}/2 + 0.175	10.0	−10.0
SSTL18_I	−0.300	V_{REF} − 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	V_{CCO}/2 − 0.470	V_{CCO}/2 + 0.470	7.0	−7.0
MIPI_DPHY_DCI_LP[6]	−0.300	0.550	0.880	V_{CCO} + 0.300	0.050	1.100	0.01	−0.01

Notes:
1. Tested according to relevant specifications.
2. Standards specified using the default I/O standard configuration. For details, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).
3. POD10 and POD12 DC input and output levels are shown in Table 11, Table 15, Table 16, and Table 17.
4. Supported drive strengths of 2, 4, 6, or 8 mA in HP I/O banks.
5. Supported drive strengths of 2, 4, 6, 8, or 12 mA in HP I/O banks.
6. Low-power option for MIPI_DPHY_DCI.

Table 11: **DC Input Levels for Single-ended POD10 and POD12 I/O Standards**[1][2]

I/O Standard	V_{IL}		V_{IH}	
	V, Min	V, Max	V, Min	V, Max
POD10	−0.300	V_{REF} − 0.068	V_{REF} + 0.068	V_{CCO} + 0.300
POD12	−0.300	V_{REF} − 0.068	V_{REF} + 0.068	V_{CCO} + 0.300

Notes:
1. Tested according to relevant specifications.
2. Standards specified using the default I/O standard configuration. For details, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).

Table 12: **Differential SelectIO DC Input and Output Levels**

I/O Standard	V_{ICM} (V)[1]			V_{ID}(V)[2]			V_{ILHS}[3]	V_{IHHS}[3]	V_{OCM}(V)[4]			V_{OD}(V)[5]		
	Min	Typ	Max	Min	Typ	Max	Min	Max	Min	Typ	Max	Min	Typ	Max
SUB_LVDS[8]	0.500	0.900	1.300	0.070	–	–	–	–	0.700	0.900	1.100	0.100	0.150	0.200
LVPECL	0.300	1.200	1.425	0.100	0.350	0.600	–	–	–	–	–	–	–	–
SLVS_400_18	0.070	0.200	0.330	0.140	–	0.450	–	–	–	–	–	–	–	–
SLVS_400_25	0.070	0.200	0.330	0.140	–	0.450	–	–	–	–	–	–	–	–
MIPI_DPHY_DCI_HS[9]	0.070	–	0.330	0.070	–	–	−0.040	0.460	0.150	0.200	0.250	0.140	0.200	0.270

Notes:

1. V_{ICM} is the input common mode voltage.
2. V_{ID} is the input differential voltage ($Q - \overline{Q}$).
3. V_{IHHS} and V_{ILHS} are the single-ended input high and low voltages, respectively.
4. V_{OCM} is the output common mode voltage.
5. V_{OD} is the output differential voltage ($Q - \overline{Q}$).
6. LVDS_25 is specified in Table 18.
7. LVDS is specified in Table 19.
8. Only the SUB_LVDS receiver is supported in HD I/O banks.
9. High-speed option for MIPI_DPHY_DCI. The V_{ID} maximum is aligned with the standard's specification. A higher V_{ID} is acceptable as long as the V_{IN} specification is also met.

Table 13: **Complementary Differential SelectIO DC Input and Output Levels for HD I/O Banks**

I/O Standard	V_{ICM} (V)[1]			V_{ID} (V)[2]		V_{OL} (V)[3]	V_{OH} (V)[4]	I_{OL}	I_{OH}
	Min	Typ	Max	Min	Max	Max	Min	mA	mA
DIFF_HSTL_I	0.300	0.750	1.125	0.100	–	0.400	$V_{CCO} - 0.400$	8.0	−8.0
DIFF_HSTL_I_18	0.300	0.900	1.425	0.100	–	0.400	$V_{CCO} - 0.400$	8.0	−8.0
DIFF_HSUL_12	0.300	0.600	0.850	0.100	–	20% V_{CCO}	80% V_{CCO}	0.1	−0.1
DIFF_SSTL12	0.300	0.600	0.850	0.100	–	$(V_{CCO}/2) - 0.150$	$(V_{CCO}/2) + 0.150$	14.25	−14.25
DIFF_SSTL135	0.300	0.675	1.000	0.100	–	$(V_{CCO}/2) - 0.150$	$(V_{CCO}/2) + 0.150$	8.9	−8.9
DIFF_SSTL135_II	0.300	0.675	1.000	0.100	–	$(V_{CCO}/2) - 0.150$	$(V_{CCO}/2) + 0.150$	13.0	−13.0
DIFF_SSTL15	0.300	0.750	1.125	0.100	–	$(V_{CCO}/2) - 0.175$	$(V_{CCO}/2) + 0.175$	8.9	−8.9
DIFF_SSTL15_II	0.300	0.750	1.125	0.100	–	$(V_{CCO}/2) - 0.175$	$(V_{CCO}/2) + 0.175$	13.0	−13.0
DIFF_SSTL18_I	0.300	0.900	1.425	0.100	–	$(V_{CCO}/2) - 0.470$	$(V_{CCO}/2) + 0.470$	8.0	−8.0
DIFF_SSTL18_II	0.300	0.900	1.425	0.100	–	$(V_{CCO}/2) - 0.600$	$(V_{CCO}/2) + 0.600$	13.4	−13.4

Notes:

1. V_{ICM} is the input common mode voltage.
2. V_{ID} is the input differential voltage.
3. V_{OL} is the single-ended low-output voltage.
4. V_{OH} is the single-ended high-output voltage.

Table 14: **Complementary Differential SelectIO DC Input and Output Levels for HP I/O Banks**[1]

| I/O Standard | V_{ICM} (V)[2] | | | V_{ID} (V)[3] | | V_{OL} (V)[4] | V_{OH} (V)[5] | I_{OL} | I_{OH} |
	Min	Typ	Max	Min	Max	Max	Min	mA	mA
DIFF_HSTL_I	0.680	$V_{CCO}/2$	$(V_{CCO}/2) + 0.150$	0.100	–	0.400	$V_{CCO} - 0.400$	5.8	−5.8
DIFF_HSTL_I_12	$0.400 \times V_{CCO}$	$V_{CCO}/2$	$0.600 \times V_{CCO}$	0.100	–	$0.250 \times V_{CCO}$	$0.750 \times V_{CCO}$	4.1	−4.1
DIFF_HSTL_I_18	$(V_{CCO}/2) - 0.175$	$V_{CCO}/2$	$(V_{CCO}/2) + 0.175$	0.100	–	0.400	$V_{CCO} - 0.400$	6.2	−6.2
DIFF_HSUL_12	$(V_{CCO}/2) - 0.120$	$V_{CCO}/2$	$(V_{CCO}/2) + 0.120$	0.100	–	20% V_{CCO}	80% V_{CCO}	0.1	−0.1
DIFF_SSTL12	$(V_{CCO}/2) - 0.150$	$V_{CCO}/2$	$(V_{CCO}/2) + 0.150$	0.100	–	$(V_{CCO}/2) - 0.150$	$(V_{CCO}/2) + 0.150$	8.0	−8.0
DIFF_SSTL135	$(V_{CCO}/2) - 0.150$	$V_{CCO}/2$	$(V_{CCO}/2) + 0.150$	0.100	–	$(V_{CCO}/2) - 0.150$	$(V_{CCO}/2) + 0.150$	9.0	−9.0
DIFF_SSTL15	$(V_{CCO}/2) - 0.175$	$V_{CCO}/2$	$(V_{CCO}/2) + 0.175$	0.100	–	$(V_{CCO}/2) - 0.175$	$(V_{CCO}/2) + 0.175$	10.0	−10.0
DIFF_SSTL18_I	$(V_{CCO}/2) - 0.175$	$V_{CCO}/2$	$(V_{CCO}/2) + 0.175$	0.100	–	$(V_{CCO}/2) - 0.470$	$(V_{CCO}/2) + 0.470$	7.0	−7.0

Notes:
1. DIFF_POD10 and DIFF_POD12 HP I/O bank specifications are shown in Table 15, Table 16, and Table 17.
2. V_{ICM} is the input common mode voltage.
3. V_{ID} is the input differential voltage.
4. V_{OL} is the single-ended low-output voltage.
5. V_{OH} is the single-ended high-output voltage.

Table 15: **DC Input Levels for Differential POD10 and POD12 I/O Standards**[1][2]

| I/O Standard | V_{ICM} (V) | | | V_{ID} (V) | |
	Min	Typ	Max	Min	Max
DIFF_POD10	0.63	0.70	0.77	0.14	–
DIFF_POD12	0.76	0.84	0.92	0.16	–

Notes:
1. Tested according to relevant specifications.
2. Standards specified using the default I/O standard configuration. For details, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).

Table 16: **DC Output Levels for Single-ended and Differential POD10 and POD12 Standards**[1][2]

Symbol	Description	V_{OUT}	Min	Typ	Max	Units
R_{OL}	Pull-down resistance.	V_{OM_DC} (as described in Table 17)	36	40	44	Ω
R_{OH}	Pull-up resistance.	V_{OM_DC} (as described in Table 17)	36	40	44	Ω

Notes:
1. Tested according to relevant specifications.
2. Standards specified using the default I/O standard configuration. For details, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).

Table 17: **Table 16 Definitions for DC Output Levels for POD Standards**

Symbol	Description	All Speed Grades	Units
V_{OM_DC}	DC output Mid measurement level (for IV curve linearity).	$0.8 \times V_{CCO}$	V

LVDS DC Specifications (LVDS_25)

The LVDS_25 standard is available in the HD I/O banks. See the *UltraScale Architecture SelectIO Resources User Guide* (UG571) for more information.

Table 18: **LVDS_25 DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}[1]	Supply voltage.		2.375	2.500	2.625	V
V_{IDIFF}	Differential input voltage: $(Q - \overline{Q})$, Q = High $(\overline{Q} - Q)$, $\overline{Q}$ = High		100	350	600[2]	mV
V_{ICM}	Input common-mode voltage.		0.300	1.200	1.425	V

Notes:

1. LVDS_25 in HD I/O banks supports inputs only. LVDS_25 inputs without internal termination have no V_{CCO} requirements. Any V_{CCO} can be chosen as long as the input voltage levels do not violate the *Recommended Operating Condition* (Table 2) specification for the V_{IN} I/O pin voltage.
2. Maximum V_{IDIFF} value is specified for the maximum V_{ICM} specification. With a lower V_{ICM}, a higher V_{DIFF} is tolerated only when the recommended operating conditions and overshoot/undershoot V_{IN} specifications are maintained.

LVDS DC Specifications (LVDS)

The LVDS standard is available in the HP I/O banks. See the *UltraScale Architecture SelectIO Resources User Guide* (UG571) for more information.

Table 19: **LVDS DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}[1]	Supply voltage.		1.710	1.800	1.890	V
V_{ODIFF}[2]	Differential output voltage: $(Q - \overline{Q})$, Q = High $(\overline{Q} - Q)$, $\overline{Q}$ = High	R_T = 100Ω across Q and $\overline{Q}$ signals	247	350	454	mV
V_{OCM}[2]	Output common-mode voltage.	R_T = 100 Ω across Q and $\overline{Q}$ signals	1.000	1.250	1.425	V
V_{IDIFF}[3]	Differential input voltage: $(Q - \overline{Q})$, Q = High $(\overline{Q} - Q)$, $\overline{Q}$ = High		100	350	600[3]	mV
V_{ICM_DC}[4]	Input common-mode voltage (DC coupling).		0.300	1.200	1.425	V
V_{ICM_AC}[5]	Input common-mode voltage (AC coupling).		0.600	–	1.100	V

Notes:

1. In HP I/O banks, when LVDS is used with input-only functionality, it can be placed in a bank where the V_{CCO} levels are different from the specified level only if internal differential termination is not used. In this scenario, V_{CCO} must be chosen to ensure the input pin voltage levels do not violate the *Recommended Operating Condition* (Table 2) specification for the V_{IN} I/O pin voltage.
2. V_{OCM} and V_{ODIFF} values are for LVDS_PRE_EMPHASIS = FALSE.
3. Maximum V_{IDIFF} value is specified for the maximum V_{ICM} specification. With a lower V_{ICM}, a higher V_{DIFF} is tolerated only when the recommended operating conditions and overshoot/undershoot V_{IN} specifications are maintained.
4. Input common mode voltage for DC coupled configurations. EQUALIZATION = EQ_NONE (Default).
5. External input common mode voltage specification for AC coupled configurations. EQUALIZATION = EQ_LEVEL0, EQ_LEVEL1, EQ_LEVEL2, EQ_LEVEL3, EQ_LEVEL4.

AC Switching Characteristics

All values represented in this data sheet are based on the speed specifications in the Vivado® Design Suite as outlined in Table 20.

Table 20: **Speed Specification Version By Device**

2017.1	Device
1.08	XCKU11P
1.10	XCKU3P, XCKU5P, XCKU9P, XCKU13P, and XCKU15P

Switching characteristics are specified on a per-speed-grade basis and can be designated as Advance, Preliminary, or Production. Each designation is defined as follows:

Advance Product Specification

These specifications are based on simulations only and are typically available soon after device design specifications are frozen. Although speed grades with this designation are considered relatively stable and conservative, some under-reporting might still occur.

Preliminary Product Specification

These specifications are based on complete ES (engineering sample) silicon characterization. Devices and speed grades with this designation are intended to give a better indication of the expected performance of production silicon. The probability of under-reporting delays is greatly reduced as compared to Advance data.

Product Specification

These specifications are released once enough production silicon of a particular device family member has been characterized to provide full correlation between specifications and devices over numerous production lots. There is no under-reporting of delays, and customers receive formal notification of any subsequent changes. Typically, the slowest speed grades transition to production before faster speed grades.

Testing of AC Switching Characteristics

Internal timing parameters are derived from measuring internal test patterns. All AC switching characteristics are representative of worst-case supply voltage and junction temperature conditions.

For more specific, more precise, and worst-case guaranteed data, use the values reported by the static timing analyzer and back-annotate to the simulation net list. Unless otherwise noted, values apply to all Kintex UltraScale+ FPGAs.

Speed Grade Designations

Since individual family members are produced at different times, the migration from one category to another depends completely on the status of the fabrication process for each device. Table 21 correlates the current status of the Kintex UltraScale+ FPGAs on a per speed grade basis.

Table 21: **Speed Grade Designations by Device**

Device	Speed Grade, Temperature Ranges, and V_{CCINT} Operating Voltages		
	Advance	**Preliminary**	**Production**
XCKU3P	-3E (V_{CCINT} = 0.90V) -2LE (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.72V)[1] -1LI (V_{CCINT} = 0.85V), -1LI (V_{CCINT} = 0.72V)[1]		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCKU5P	-3E (V_{CCINT} = 0.90V) -2LE (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.72V)[1] -1LI (V_{CCINT} = 0.85V), -1LI (V_{CCINT} = 0.72V)[1]		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCKU9P	-3E (V_{CCINT} = 0.90V) -2LE (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.72V)[1] -1LI (V_{CCINT} = 0.85V), -1LI (V_{CCINT} = 0.72V)[1]	-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)	
XCKU11P	-3E (V_{CCINT} = 0.90V) -2E (V_{CCINT} = 0.85V), -2I (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V)[1], -1LI (V_{CCINT} = 0.72V)[1]		
XCKU13P	-3E (V_{CCINT} = 0.90V) -2E (V_{CCINT} = 0.85V), -2I (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V)[1], -1LI (V_{CCINT} = 0.72V)[1]		
XCKU15P	-3E (V_{CCINT} = 0.90V) -2E (V_{CCINT} = 0.85V), -2I (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V)[1], -1LI (V_{CCINT} = 0.72V)[1]		

Notes:
1. The lowest power -1L and -2L devices, where V_{CCINT} = 0.72V, are listed in the Vivado Design Suite as -1LV and -2LV respectively.

Production Silicon and Software Status

In some cases, a particular family member (and speed grade) is released to production before a speed specification is released with the correct label (Advance, Preliminary, Production). Any labeling discrepancies are corrected in subsequent speed specification releases.

Table 22 lists the production released Kintex UltraScale+ FPGAs, speed grade, and the minimum corresponding supported speed specification version and Vivado software revisions. The Vivado software and speed specifications listed are the minimum releases required for production. All subsequent releases of software and speed specifications are valid.

Table 22: **Kintex UltraScale+ FPGA Device Production Software and Speed Specification Release**

Device	Speed Grade and V_{CCINT} Operating Voltages						
	0.90V	0.85V				0.72V	
	-3	-2	-1	-2L	-1L	-2L	-1L
XCKU3P		Vivado tools 2017.1 v1.10					
XCKU5P		Vivado tools 2017.1 v1.10					
XCKU9P							
XCKU11P							
XCKU13P							
XCKU15P							

Notes:
1. Blank entries indicate a device and/or speed grade in Advance or Preliminary status.

FPGA Logic Performance Characteristics

This section provides the performance characteristics of some common functions and designs implemented in Kintex UltraScale+ FPGAs. These values are subject to the same guidelines as the AC Switching Characteristics, page 16. In each table, the I/O bank type is either high performance (HP) or high density (HD).

Table 23: **LVDS Component Mode Performance**

Description	I/O Bank Type	Speed Grade and V_{CCINT} Operating Voltages										Units
		0.90V		0.85V				0.72V				
		-3		-2		-1		-2		-1		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
LVDS TX DDR (OSERDES 4:1, 8:1)	HP	0	1250	0	1250	0	1250	0	1250	0	1250	Mb/s
LVDS TX SDR (OSERDES 2:1, 4:1)	HP	0	625	0	625	0	625	0	625	0	625	Mb/s
LVDS RX DDR (ISERDES 1:4, 1:8)[1]	HP	0	1250	0	1250	0	1250	0	1250	0	1250	Mb/s
LVDS RX DDR	HD	0	250	0	250	0	250	0	250	0	250	Mb/s
LVDS RX SDR (ISERDES 1:2, 1:4)[1]	HP	0	625	0	625	0	625	0	625	0	625	Mb/s
LVDS RX SDR	HD	0	125	0	125	0	125	0	125	0	125	Mb/s

Notes:
1. LVDS receivers are typically bounded with certain applications to achieve maximum performance. Package skews are not included and should be removed through PCB routing.

Table 24: **LVDS Native Mode Performance**[1][2]

Description	DATA_WIDTH	I/O Bank Type	Speed Grade and V_{CCINT} Operating Voltages										Units
			0.90V		0.85V				0.72V				
			-3		-2		-1		-2		-1		
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
LVDS TX DDR (TX_BITSLICE)	4	HP	375	1600	375	1600	375	1260	375	1400	375	1260	Mb/s
	8		375	1600	375	1600	375	1260	375	1600	375	1260	Mb/s
LVDS TX SDR (TX_BITSLICE)	4	HP	187.5	800	187.5	800	187.5	630	187.5	700	187.5	630	Mb/s
	8		187.5	800	187.5	800	187.5	630	187.5	800	187.5	630	Mb/s
LVDS RX DDR (RX_BITSLICE)[3]	4	HP	375	1600	375	1600	375	1260	375	1400	375	1260	Mb/s
	8		375	1600	375	1600	375	1260	375	1600	375	1260	Mb/s
LVDS RX SDR (RX_BITSLICE)[3]	4	HP	187.5	800	187.5	800	187.5	630	187.5	700	187.5	630	Mb/s
	8		187.5	800	187.5	800	187.5	630	187.5	800	187.5	630	Mb/s

Notes:
1. Native mode is supported through the High-Speed SelectIO Interface Wizard available with the Vivado Design Suite. The performance values assume a source-synchronous interface.
2. PLL settings can restrict the minimum allowable data rate. For example, when using the PLL with CLKOUTPHY_MODE = VCO_HALF the minimum frequency is PLL_FVCOMIN/2.
3. LVDS receivers are typically bounded with certain applications to achieve maximum performance. Package skews are not included and should be removed through PCB routing.

Table 25: **MIPI D-PHY Performance**

Description	I/O Bank Type	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
MIPI D-PHY transmitter or receiver.	HP	1500	1500	1260	1260	1260	Mb/s

Table 26: **LVDS Native-Mode 1000BASE-X Support[1]**

Description	I/O Bank Type	Speed Grade and V_{CCINT} Operating Voltages				
		0.90V	0.85V		0.72V	
		-3	-2	-1	-2	-1
1000BASE-X	HP	Yes				

Notes:

1. 1000BASE-X support is based on the *IEEE Standard for CSMA/CD Access Method and Physical Layer Specifications* (IEEE Std 802.3-2008).

Table 27 provides the maximum data rates for applicable memory standards using the Kintex UltraScale+ FPGA memory PHY. Refer to Memory Interfaces for the complete list of memory interface standards supported and detailed specifications. The final performance of the memory interface is determined through a complete design implemented in the Vivado Design Suite, following guidelines in the *UltraScale Architecture PCB Design Guide* (UG583), electrical analysis, and characterization of the system.

Table 27: **Maximum Physical Interface (PHY) Rate for Memory Interfaces**

Memory Standard	Package	DRAM Type	Speed Grade and V_{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
DDR4	All FFV packages	Single rank component	2666	2666	2400	2400	2133	Mb/s
		1 rank DIMM[1][2][3]	2400	2400	2133	2133	1866	Mb/s
		2 rank DIMM[1][4]	2133	2133	1866	1866	1600	Mb/s
		4 rank DIMM[1][5]	1600	1600	1333	1333	N/A	Mb/s
	SFVB784	Single rank component	2400	2400	2133	2133	1866	Mb/s
		1 rank DIMM[1][2]	2133	2133	1866	1866	1600	Mb/s
		2 rank DIMM[1][4]	1866	1866	1600	1600	1600	Mb/s
DDR3	All FFV packages	Single rank component	2133	2133	2133	2133	1866	Mb/s
		1 rank DIMM[1][2]	1866	1866	1866	1866	1600	Mb/s
		2 rank DIMM[1][4]	1600	1600	1600	1600	1333	Mb/s
		4 rank DIMM[1][5]	1066	1066	1066	1066	800	Mb/s
	SFVB784	Single rank component	1866	1866	1866	1866	1600	Mb/s
		1 rank DIMM[1][2]	1600	1600	1600	1600	1600	Mb/s
		2 rank DIMM[1][4]	1600	1600	1600	1600	1333	Mb/s
		4 rank DIMM[1][5]	1066	1066	1066	1066	800	Mb/s

Table 27: **Maximum Physical Interface (PHY) Rate for Memory Interfaces** *(Cont'd)*

Memory Standard	Package	DRAM Type	Speed Grade and V_{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
DDR3L	All FFV packages	Single rank component	1866	1866	1866	1866	1600	Mb/s
		1 rank DIMM[1][2]	1600	1600	1600	1600	1333	Mb/s
		2 rank DIMM[1][3]	1333	1333	1333	1333	1066	Mb/s
		4 rank DIMM[1][5]	800	800	800	800	606	Mb/s
	SFVB784	Single rank component	1600	1600	1600	1600	1600	Mb/s
		1 rank DIMM[1][2]	1600	1600	1600	1600	1333	Mb/s
		2 rank DIMM[1][4]	1333	1333	1333	1333	1066	Mb/s
		4 rank DIMM[1][5]	800	800	800	800	606	Mb/s
QDR II+	All	Single rank component[6]	633	633	600	600	550	MHz
RLDRAM 3	All FFV packages	Single rank component	1200	1200	1066	1066	933	MHz
	SFVB784	Single rank component	1066	1066	933	933	800	MHz
QDR IV XP	All	Single rank component	1066	1066	1066	933	933	MHz
LPDDR3	All	Single rank component	1600	1600	1600	1600	1600	Mb/s

Notes:
1. Dual in-line memory module (DIMM) includes RDIMM, SODIMM, UDIMM, and LRDIMM.
2. Includes: 1 rank 1 slot, DDP 2 rank, LRDIMM 2 or 4 rank 1 slot.
3. For the DDR4 DDP components at -3 and -2 speed grades and V_{CCINT} = 0.85V, the maximum data rate is 2133 Mb/s for six or more DDP devices. For five or less DDP devices, use the single rank DIMM data rates for the -3 and -2 speed grades at 0.85V.
4. Includes: 2 rank 1 slot, 1 rank 2 slot, LRDIMM 2 rank 2 slot.
5. Includes: 2 rank 2 slot, 4 rank 1 slot.
6. The QDRII+ performance specifications are for burst-length 4 (BL = 4) implementations.

FPGA Logic Switching Characteristics

Table 28 (high-density IOB (HD)) and Table 29 (high-performance IOB (HP)) summarizes the values of standard-specific data input delay adjustments, output delays terminating at pads (based on standard) and 3-state delays.

- $T_{INBUF\_DELAY\_PAD\_I}$ is the delay from IOB pad through the input buffer to the I-pin of an IOB pad. The delay varies depending on the capability of the SelectIO input buffer.

- $T_{OUTBUF\_DELAY\_O\_PAD}$ is the delay from the O pin to the IOB pad through the output buffer of an IOB pad. The delay varies depending on the capability of the SelectIO output buffer.

- $T_{OUTBUF\_DELAY\_TD\_PAD}$ is the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is disabled. The delay varies depending on the SelectIO capability of the output buffer. In HP I/O banks, the internal DCI termination turn-on time is always faster than $T_{OUTBUF\_DELAY\_TD\_PAD}$ when the DCITERMDISABLE pin is used. In HD I/O banks, the on-die termination turn-on time is always faster than $T_{OUTBUF\_DELAY\_TD\_PAD}$ when the INTERMDISABLE pin is used.

IOB High Density (HD) Switching Characteristics

Table 28: **IOB High Density (HD) Switching Characteristics**

I/O Standards	$T_{INBUF\_DELAY\_PAD\_I}$					$T_{OUTBUF\_DELAY\_O\_PAD}$					$T_{OUTBUF\_DELAY\_TD\_PAD}$					Units
	0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		
	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	
DIFF_HSTL_I_18_F	0.978	0.978	1.058	0.978	1.058	1.574	1.574	1.718	1.574	1.718	1.160	1.160	1.271	1.160	1.271	ns
DIFF_HSTL_I_18_S	0.978	0.978	1.058	0.978	1.058	1.805	1.805	1.950	1.805	1.950	1.748	1.748	1.867	1.748	1.867	ns
DIFF_HSTL_I_F	0.978	0.978	1.058	0.978	1.058	1.611	1.611	1.762	1.611	1.762	1.313	1.313	1.417	1.313	1.417	ns
DIFF_HSTL_I_S	0.978	0.978	1.058	0.978	1.058	1.798	1.798	1.913	1.798	1.913	1.630	1.630	1.780	1.630	1.780	ns
DIFF_HSUL_12_F	0.911	0.911	0.977	0.911	0.977	1.573	1.573	1.703	1.573	1.703	1.222	1.222	1.335	1.222	1.335	ns
DIFF_HSUL_12_S	0.911	0.911	0.977	0.911	0.977	1.711	1.711	1.864	1.711	1.864	1.536	1.536	1.665	1.536	1.665	ns
DIFF_SSTL12_F	0.906	0.906	0.977	0.906	0.977	1.643	1.643	1.792	1.643	1.792	1.285	1.285	1.423	1.285	1.423	ns
DIFF_SSTL12_S	0.906	0.906	0.977	0.906	0.977	1.784	1.784	1.948	1.784	1.948	1.567	1.567	1.706	1.567	1.706	ns
DIFF_SSTL135_F	0.927	0.927	0.995	0.927	0.995	1.625	1.625	1.765	1.625	1.765	1.341	1.341	1.458	1.341	1.458	ns
DIFF_SSTL135_II_F	0.927	0.927	0.995	0.927	0.995	1.623	1.623	1.770	1.623	1.770	1.325	1.325	1.470	1.325	1.470	ns
DIFF_SSTL135_II_S	0.927	0.927	0.995	0.927	0.995	1.768	1.768	1.916	1.768	1.916	1.722	1.722	1.911	1.722	1.911	ns
DIFF_SSTL135_S	0.927	0.927	0.995	0.927	0.995	1.869	1.869	2.025	1.869	2.025	1.814	1.814	1.976	1.814	1.976	ns
DIFF_SSTL15_F	0.928	0.928	1.020	0.928	1.020	1.628	1.628	1.771	1.628	1.771	1.374	1.374	1.483	1.374	1.483	ns
DIFF_SSTL15_II_F	0.928	0.928	1.020	0.928	1.020	1.622	1.622	1.778	1.622	1.778	1.356	1.356	1.442	1.356	1.442	ns
DIFF_SSTL15_II_S	0.928	0.928	1.020	0.928	1.020	1.821	1.821	1.987	1.821	1.987	1.895	1.895	2.047	1.895	2.047	ns
DIFF_SSTL15_S	0.928	0.928	1.020	0.928	1.020	1.824	1.824	1.977	1.824	1.977	1.743	1.743	1.907	1.743	1.907	ns
DIFF_SSTL18_II_F	0.961	0.961	1.038	0.961	1.038	1.729	1.729	1.880	1.729	1.880	1.377	1.377	1.492	1.377	1.492	ns
DIFF_SSTL18_II_S	0.961	0.961	1.038	0.961	1.038	1.796	1.796	1.965	1.796	1.965	1.616	1.616	1.800	1.616	1.800	ns
DIFF_SSTL18_I_F	0.961	0.961	1.038	0.961	1.038	1.609	1.609	1.755	1.609	1.755	1.220	1.220	1.313	1.220	1.313	ns
DIFF_SSTL18_I_S	0.961	0.961	1.038	0.961	1.038	1.786	1.786	1.942	1.786	1.942	1.677	1.677	1.836	1.677	1.836	ns
HSTL_I_18_F	0.947	0.947	1.021	0.947	1.021	1.574	1.574	1.718	1.574	1.718	1.160	1.160	1.271	1.160	1.271	ns
HSTL_I_18_S	0.947	0.947	1.021	0.947	1.021	1.805	1.805	1.950	1.805	1.950	1.748	1.748	1.867	1.748	1.867	ns

Table 28: **IOB High Density (HD) Switching Characteristics** *(Cont'd)*

I/O Standards	T_INBUF_DELAY_PAD_I					T_OUTBUF_DELAY_O_PAD					T_OUTBUF_DELAY_TD_PAD					Units
	0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		
	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	
HSTL_I_F	0.856	0.856	0.900	0.856	0.900	1.611	1.611	1.762	1.611	1.762	1.313	1.313	1.417	1.313	1.417	ns
HSTL_I_S	0.856	0.856	0.900	0.856	0.900	1.798	1.798	1.913	1.798	1.913	1.630	1.630	1.780	1.630	1.780	ns
HSUL_12_F	0.780	0.780	0.867	0.780	0.867	1.573	1.573	1.703	1.573	1.703	1.222	1.222	1.335	1.222	1.335	ns
HSUL_12_S	0.780	0.780	0.867	0.780	0.867	1.711	1.711	1.864	1.711	1.864	1.536	1.536	1.665	1.536	1.665	ns
LVCMOS12_F_12	0.918	0.918	0.976	0.918	0.976	1.689	1.689	1.856	1.689	1.856	1.202	1.202	1.317	1.202	1.317	ns
LVCMOS12_F_4	0.918	0.918	0.976	0.918	0.976	1.742	1.742	1.922	1.742	1.922	1.353	1.353	1.478	1.353	1.478	ns
LVCMOS12_F_8	0.918	0.918	0.976	0.918	0.976	1.714	1.714	1.879	1.714	1.879	1.292	1.292	1.432	1.292	1.432	ns
LVCMOS12_S_12	0.918	0.918	0.976	0.918	0.976	2.073	2.073	2.247	2.073	2.247	1.581	1.581	1.717	1.581	1.717	ns
LVCMOS12_S_4	0.918	0.918	0.976	0.918	0.976	1.979	1.979	2.182	1.979	2.182	1.633	1.633	1.772	1.633	1.772	ns
LVCMOS12_S_8	0.918	0.918	0.976	0.918	0.976	2.205	2.205	2.406	2.205	2.406	1.767	1.767	1.928	1.767	1.928	ns
LVCMOS15_F_12	0.905	0.905	0.958	0.905	0.958	1.713	1.713	1.892	1.713	1.892	1.275	1.275	1.428	1.275	1.428	ns
LVCMOS15_F_16	0.905	0.905	0.958	0.905	0.958	1.722	1.722	1.881	1.722	1.881	1.260	1.260	1.407	1.260	1.407	ns
LVCMOS15_F_4	0.905	0.905	0.958	0.905	0.958	1.825	1.825	1.959	1.825	1.959	1.453	1.453	1.557	1.453	1.557	ns
LVCMOS15_F_8	0.905	0.905	0.958	0.905	0.958	1.778	1.778	1.930	1.778	1.930	1.378	1.378	1.458	1.378	1.458	ns
LVCMOS15_S_12	0.905	0.905	0.958	0.905	0.958	1.991	1.991	2.139	1.991	2.139	1.516	1.516	1.648	1.516	1.648	ns
LVCMOS15_S_16	0.905	0.905	0.958	0.905	0.958	2.172	2.172	2.389	2.172	2.389	1.707	1.707	1.888	1.707	1.888	ns
LVCMOS15_S_4	0.905	0.905	0.958	0.905	0.958	2.313	2.313	2.483	2.313	2.483	1.952	1.952	2.123	1.952	2.123	ns
LVCMOS15_S_8	0.905	0.905	0.958	0.905	0.958	2.170	2.170	2.400	2.170	2.400	1.817	1.817	1.984	1.817	1.984	ns
LVCMOS18_F_12	0.915	0.915	0.958	0.915	0.958	1.805	1.805	1.962	1.805	1.962	1.383	1.383	1.471	1.383	1.471	ns
LVCMOS18_F_16	0.915	0.915	0.958	0.915	0.958	1.785	1.785	1.917	1.785	1.917	1.338	1.338	1.446	1.338	1.446	ns
LVCMOS18_F_4	0.915	0.915	0.958	0.915	0.958	1.868	1.868	2.013	1.868	2.013	1.472	1.472	1.599	1.472	1.599	ns
LVCMOS18_F_8	0.915	0.915	0.958	0.915	0.958	1.797	1.797	1.979	1.797	1.979	1.384	1.384	1.487	1.384	1.487	ns
LVCMOS18_S_12	0.915	0.915	0.958	0.915	0.958	2.201	2.201	2.408	2.201	2.408	1.762	1.762	1.894	1.762	1.894	ns
LVCMOS18_S_16	0.915	0.915	0.958	0.915	0.958	2.173	2.173	2.362	2.173	2.362	1.702	1.702	1.834	1.702	1.834	ns
LVCMOS18_S_4	0.915	0.915	0.958	0.915	0.958	2.346	2.346	2.567	2.346	2.567	1.951	1.951	2.092	1.951	2.092	ns
LVCMOS18_S_8	0.915	0.915	0.958	0.915	0.958	2.292	2.292	2.511	2.292	2.511	1.848	1.848	2.008	1.848	2.008	ns
LVCMOS25_F_12	0.988	0.988	1.042	0.988	1.042	2.153	2.153	2.453	2.153	2.453	1.692	1.692	1.856	1.692	1.856	ns
LVCMOS25_F_16	0.988	0.988	1.042	0.988	1.042	2.105	2.105	2.406	2.105	2.406	1.623	1.623	1.786	1.623	1.786	ns
LVCMOS25_F_4	0.988	0.988	1.042	0.988	1.042	2.344	2.344	2.554	2.344	2.554	1.842	1.842	2.039	1.842	2.039	ns
LVCMOS25_F_8	0.988	0.988	1.042	0.988	1.042	2.184	2.184	2.516	2.184	2.516	1.726	1.726	1.910	1.726	1.910	ns
LVCMOS25_S_12	0.988	0.988	1.042	0.988	1.042	2.558	2.558	2.840	2.558	2.840	1.971	1.971	2.194	1.971	2.194	ns
LVCMOS25_S_16	0.988	0.988	1.042	0.988	1.042	2.449	2.449	2.740	2.449	2.740	1.852	1.852	2.063	1.852	2.063	ns
LVCMOS25_S_4	0.988	0.988	1.042	0.988	1.042	2.770	2.770	3.066	2.770	3.066	2.224	2.224	2.458	2.224	2.458	ns
LVCMOS25_S_8	0.988	0.988	1.042	0.988	1.042	2.663	2.663	2.963	2.663	2.963	2.091	2.091	2.373	2.091	2.373	ns
LVCMOS33_F_12	1.154	1.154	1.213	1.154	1.213	2.415	2.415	2.651	2.415	2.651	1.754	1.754	1.915	1.754	1.915	ns
LVCMOS33_F_16	1.154	1.154	1.213	1.154	1.213	2.383	2.383	2.603	2.383	2.603	1.734	1.734	1.869	1.734	1.869	ns
LVCMOS33_F_4	1.154	1.154	1.213	1.154	1.213	2.541	2.541	2.765	2.541	2.765	1.932	1.932	2.135	1.932	2.135	ns
LVCMOS33_F_8	1.154	1.154	1.213	1.154	1.213	2.603	2.603	2.822	2.603	2.822	1.937	1.937	2.130	1.937	2.130	ns
LVCMOS33_S_12	1.154	1.154	1.213	1.154	1.213	2.705	2.705	3.047	2.705	3.047	2.049	2.049	2.318	2.049	2.318	ns
LVCMOS33_S_16	1.154	1.154	1.213	1.154	1.213	2.714	2.714	3.024	2.714	3.024	2.028	2.028	2.232	2.028	2.232	ns
LVCMOS33_S_4	1.154	1.154	1.213	1.154	1.213	2.999	2.999	3.340	2.999	3.340	2.320	2.320	2.610	2.320	2.610	ns

Table 28: **IOB High Density (HD) Switching Characteristics** *(Cont'd)*

I/O Standards	T_INBUF_DELAY_PAD_I					T_OUTBUF_DELAY_O_PAD					T_OUTBUF_DELAY_TD_PAD					Units
	0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		
	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	
LVCMOS33_S_8	1.154	1.154	1.213	1.154	1.213	2.929	2.929	3.260	2.929	3.260	2.260	2.260	2.532	2.260	2.532	ns
LVDS_25	1.003	1.003	1.116	1.003	1.116	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	ns
LVPECL	1.003	1.003	1.116	1.003	1.116	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	ns
LVTTL_F_12	1.164	1.164	1.223	1.164	1.223	2.415	2.415	2.651	2.415	2.651	1.754	1.754	1.915	1.754	1.915	ns
LVTTL_F_16	1.164	1.164	1.223	1.164	1.223	2.464	2.464	2.732	2.464	2.732	1.750	1.750	1.986	1.750	1.986	ns
LVTTL_F_4	1.164	1.164	1.223	1.164	1.223	2.541	2.541	2.765	2.541	2.765	1.932	1.932	2.135	1.932	2.135	ns
LVTTL_F_8	1.164	1.164	1.223	1.164	1.223	2.582	2.582	2.787	2.582	2.787	1.910	1.910	2.063	1.910	2.063	ns
LVTTL_S_12	1.164	1.164	1.223	1.164	1.223	2.731	2.731	3.075	2.731	3.075	2.072	2.072	2.343	2.072	2.343	ns
LVTTL_S_16	1.164	1.164	1.223	1.164	1.223	2.714	2.714	3.024	2.714	3.024	2.028	2.028	2.232	2.028	2.232	ns
LVTTL_S_4	1.164	1.164	1.223	1.164	1.223	2.999	2.999	3.340	2.999	3.340	2.320	2.320	2.610	2.320	2.610	ns
LVTTL_S_8	1.164	1.164	1.223	1.164	1.223	2.929	2.929	3.260	2.929	3.260	2.260	2.260	2.532	2.260	2.532	ns
SLVS_400_25	1.020	1.020	1.136	1.020	1.136	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	ns
SSTL12_F	0.780	0.780	0.867	0.780	0.867	1.643	1.643	1.792	1.643	1.792	1.285	1.285	1.423	1.285	1.423	ns
SSTL12_S	0.780	0.780	0.867	0.780	0.867	1.784	1.784	1.948	1.784	1.948	1.567	1.567	1.706	1.567	1.706	ns
SSTL135_F	0.798	0.798	0.881	0.798	0.881	1.625	1.625	1.765	1.625	1.765	1.341	1.341	1.458	1.341	1.458	ns
SSTL135_II_F	0.798	0.798	0.881	0.798	0.881	1.623	1.623	1.770	1.623	1.770	1.325	1.325	1.470	1.325	1.470	ns
SSTL135_II_S	0.798	0.798	0.881	0.798	0.881	1.768	1.768	1.916	1.768	1.916	1.722	1.722	1.911	1.722	1.911	ns
SSTL135_S	0.798	0.798	0.881	0.798	0.881	1.869	1.869	2.025	1.869	2.025	1.814	1.814	1.976	1.814	1.976	ns
SSTL15_F	0.838	0.838	0.880	0.838	0.880	1.612	1.612	1.754	1.612	1.754	1.357	1.357	1.464	1.357	1.464	ns
SSTL15_II_F	0.838	0.838	0.880	0.838	0.880	1.622	1.622	1.778	1.622	1.778	1.356	1.356	1.442	1.356	1.442	ns
SSTL15_II_S	0.838	0.838	0.880	0.838	0.880	1.821	1.821	1.987	1.821	1.987	1.895	1.895	2.047	1.895	2.047	ns
SSTL15_S	0.838	0.838	0.880	0.838	0.880	1.824	1.824	1.977	1.824	1.977	1.743	1.743	1.907	1.743	1.907	ns
SSTL18_II_F	0.947	0.947	1.021	0.947	1.021	1.729	1.729	1.880	1.729	1.880	1.377	1.377	1.492	1.377	1.492	ns
SSTL18_II_S	0.947	0.947	1.021	0.947	1.021	1.796	1.796	1.965	1.796	1.965	1.616	1.616	1.800	1.616	1.800	ns
SSTL18_I_F	0.947	0.947	1.021	0.947	1.021	1.609	1.609	1.755	1.609	1.755	1.220	1.220	1.313	1.220	1.313	ns
SSTL18_I_S	0.947	0.947	1.021	0.947	1.021	1.786	1.786	1.942	1.786	1.942	1.677	1.677	1.836	1.677	1.836	ns
SUB_LVDS	1.002	1.002	1.036	1.002	1.036	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	ns

IOB High Performance (HP) Switching Characteristics

Table 29: **IOB High Performance (HP) Switching Characteristics**

I/O Standards	$T_{INBUF\_DELAY\_PAD\_I}$					$T_{OUTBUF\_DELAY\_O\_PAD}$					$T_{OUTBUF\_DELAY\_TD\_PAD}$					Units
	0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		
	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	
DIFF_HSTL_I_12_F	0.394	0.394	0.402	0.394	0.402	0.423	0.423	0.443	0.423	0.443	0.553	0.553	0.582	0.553	0.582	ns
DIFF_HSTL_I_12_M	0.394	0.394	0.402	0.394	0.402	0.552	0.552	0.583	0.552	0.583	0.641	0.641	0.679	0.641	0.679	ns
DIFF_HSTL_I_12_S	0.394	0.394	0.402	0.394	0.402	0.752	0.752	0.800	0.752	0.800	0.813	0.813	0.868	0.813	0.868	ns
DIFF_HSTL_I_18_F	0.319	0.319	0.339	0.319	0.339	0.456	0.456	0.474	0.456	0.474	0.576	0.576	0.606	0.576	0.606	ns
DIFF_HSTL_I_18_M	0.319	0.319	0.339	0.319	0.339	0.570	0.570	0.603	0.570	0.603	0.653	0.653	0.692	0.653	0.692	ns
DIFF_HSTL_I_18_S	0.319	0.319	0.339	0.319	0.339	0.782	0.782	0.834	0.782	0.834	0.816	0.816	0.871	0.816	0.871	ns
DIFF_HSTL_I_DCI_12_F	0.394	0.394	0.402	0.394	0.402	0.406	0.406	0.429	0.406	0.429	0.534	0.534	0.564	0.534	0.564	ns
DIFF_HSTL_I_DCI_12_M	0.394	0.394	0.402	0.394	0.402	0.557	0.557	0.587	0.557	0.587	0.653	0.653	0.694	0.653	0.694	ns
DIFF_HSTL_I_DCI_12_S	0.394	0.394	0.402	0.394	0.402	0.755	0.755	0.806	0.755	0.806	0.842	0.842	0.907	0.842	0.907	ns
DIFF_HSTL_I_DCI_18_F	0.323	0.323	0.339	0.323	0.339	0.445	0.445	0.461	0.445	0.461	0.566	0.566	0.595	0.566	0.595	ns
DIFF_HSTL_I_DCI_18_M	0.323	0.323	0.339	0.323	0.339	0.555	0.555	0.586	0.555	0.586	0.643	0.643	0.684	0.643	0.684	ns
DIFF_HSTL_I_DCI_18_S	0.323	0.323	0.339	0.323	0.339	0.762	0.762	0.818	0.762	0.818	0.836	0.836	0.900	0.836	0.900	ns
DIFF_HSTL_I_DCI_F	0.397	0.397	0.417	0.397	0.417	0.431	0.431	0.445	0.431	0.445	0.555	0.555	0.575	0.555	0.575	ns
DIFF_HSTL_I_DCI_M	0.397	0.397	0.417	0.397	0.417	0.553	0.553	0.583	0.553	0.583	0.644	0.644	0.684	0.644	0.684	ns
DIFF_HSTL_I_DCI_S	0.397	0.397	0.417	0.397	0.417	0.767	0.767	0.823	0.767	0.823	0.848	0.848	0.912	0.848	0.912	ns
DIFF_HSTL_I_F	0.404	0.404	0.417	0.404	0.417	0.423	0.423	0.443	0.423	0.443	0.549	0.549	0.581	0.549	0.581	ns
DIFF_HSTL_I_M	0.404	0.404	0.417	0.404	0.417	0.555	0.555	0.586	0.555	0.586	0.640	0.640	0.677	0.640	0.677	ns
DIFF_HSTL_I_S	0.404	0.404	0.417	0.404	0.417	0.767	0.767	0.818	0.767	0.818	0.811	0.811	0.866	0.811	0.866	ns
DIFF_HSUL_12_DCI_F	0.381	0.381	0.400	0.381	0.400	0.425	0.425	0.443	0.425	0.443	0.558	0.558	0.586	0.558	0.586	ns
DIFF_HSUL_12_DCI_M	0.381	0.381	0.400	0.381	0.400	0.557	0.557	0.587	0.557	0.587	0.653	0.653	0.694	0.653	0.694	ns
DIFF_HSUL_12_DCI_S	0.381	0.381	0.400	0.381	0.400	0.737	0.737	0.787	0.737	0.787	0.822	0.822	0.885	0.822	0.885	ns
DIFF_HSUL_12_F	0.394	0.394	0.402	0.394	0.402	0.412	0.412	0.430	0.412	0.430	0.538	0.538	0.566	0.538	0.566	ns
DIFF_HSUL_12_M	0.394	0.394	0.402	0.394	0.402	0.552	0.552	0.583	0.552	0.583	0.641	0.641	0.679	0.641	0.679	ns
DIFF_HSUL_12_S	0.394	0.394	0.402	0.394	0.402	0.752	0.752	0.800	0.752	0.800	0.813	0.813	0.868	0.813	0.868	ns
DIFF_POD10_DCI_F	0.411	0.411	0.430	0.411	0.430	0.425	0.425	0.444	0.425	0.444	0.555	0.555	0.584	0.555	0.584	ns
DIFF_POD10_DCI_M	0.411	0.411	0.430	0.411	0.430	0.542	0.542	0.571	0.542	0.571	0.640	0.640	0.681	0.640	0.681	ns
DIFF_POD10_DCI_S	0.411	0.411	0.430	0.411	0.430	0.754	0.754	0.815	0.754	0.815	0.850	0.850	0.917	0.850	0.917	ns
DIFF_POD10_F	0.411	0.411	0.433	0.411	0.433	0.438	0.438	0.459	0.438	0.459	0.569	0.569	0.601	0.569	0.601	ns
DIFF_POD10_M	0.411	0.411	0.433	0.411	0.433	0.538	0.538	0.568	0.538	0.568	0.630	0.630	0.667	0.630	0.667	ns
DIFF_POD10_S	0.411	0.411	0.433	0.411	0.433	0.766	0.766	0.821	0.766	0.821	0.836	0.836	0.894	0.836	0.894	ns
DIFF_POD12_DCI_F	0.407	0.407	0.432	0.407	0.432	0.425	0.425	0.443	0.425	0.443	0.558	0.558	0.586	0.558	0.586	ns
DIFF_POD12_DCI_M	0.407	0.407	0.432	0.407	0.432	0.543	0.543	0.572	0.543	0.572	0.638	0.638	0.678	0.638	0.678	ns
DIFF_POD12_DCI_S	0.407	0.407	0.432	0.407	0.432	0.772	0.772	0.822	0.772	0.822	0.862	0.862	0.929	0.862	0.929	ns
DIFF_POD12_F	0.409	0.409	0.430	0.409	0.430	0.455	0.455	0.476	0.455	0.476	0.595	0.595	0.626	0.595	0.626	ns
DIFF_POD12_M	0.409	0.409	0.430	0.409	0.430	0.551	0.551	0.582	0.551	0.582	0.641	0.641	0.679	0.641	0.679	ns
DIFF_POD12_S	0.409	0.409	0.430	0.409	0.430	0.767	0.767	0.817	0.767	0.817	0.832	0.832	0.889	0.832	0.889	ns
DIFF_SSTL12_DCI_F	0.381	0.381	0.400	0.381	0.400	0.425	0.425	0.443	0.425	0.443	0.558	0.558	0.586	0.558	0.586	ns
DIFF_SSTL12_DCI_M	0.381	0.381	0.400	0.381	0.400	0.557	0.557	0.587	0.557	0.587	0.654	0.654	0.694	0.654	0.694	ns
DIFF_SSTL12_DCI_S	0.381	0.381	0.400	0.381	0.400	0.754	0.754	0.803	0.754	0.803	0.842	0.842	0.908	0.842	0.908	ns

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